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Alexey A. Belyanin

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Contents

ix Conference Committee

QUANTUM DOTS

- 9002 04 **Development of broad spectral bandwidth hybrid QW/QD structures from 1000-1400 nm [9002-3]**
N. Peyvast, S. Chen, K. Zhou, N. Babazadeh, A. A. Khozim, Z. Zhang, D. T. D. Childs, O. Wada, M. Hugues, R. A. Hogg, The Univ. of Sheffield (United Kingdom); T. Kageyama, K. Nishi, K. Takemasa, M. Sugawara, QD Laser, Inc. (Japan)

NEW MATERIALS AND GRATING CONTROLLED

- 9002 08 **Red emitting monolithic dual wavelength DBR diode lasers for shifted excitation Raman difference spectroscopy [9002-7]**
B. Sumpf, M. Maiwald, A. Müller, F. Bugge, J. Fricke, P. Ressel, J. Pohl, G. Erbert, G. Tränkle, Ferdinand-Braun-Institut (Germany)
- 9002 09 **Bragg-grating-stabilized external cavity lasers for gas sensing using tunable diode laser spectroscopy [9002-8]**
S. G. Lynch, Univ. of Southampton (United Kingdom); F. Chen, Cranfield Univ. (United Kingdom); J. C. Gates, C. Holmes, Univ. of Southampton (United Kingdom); S. E. Staines, S. W. James, J. Hodgkinson, Cranfield Univ. (United Kingdom); P. G. R. Smith, Univ. of Southampton (United Kingdom); R. P. Tatam, Cranfield Univ. (United Kingdom)
- 9002 0A **Properties of 62x nm red-emitting single-mode diode lasers [9002-9]**
K. Paschke, J. Pohl, D. Feise, G. Blume, G. Erbert, Ferdinand-Braun-Institut (Germany)

MODE LOCKED

- 9002 0C **Mode-locked InAs/InP quantum-dash-based DBR laser with monolithically integrated SOA (Invited Paper) [9002-11]**
S. Joshi, N. Chimot, S. Barbet, A. Accard, F. Lelarge, III-V Lab., Thales Research and Technology (France), and CEA-LETI (France)
- 9002 0D **Femtosecond semiconductor laser system with arbitrary intracavity phase and amplitude manipulation [9002-12]**
J. C. Balzer, B. Döpke, Ruhr-Univ. Bochum (Germany); A. Klehr, G. Erbert, G. Tränkle, Ferdinand-Braun-Institut (Germany); M. R. Hofmann, Ruhr-Univ. Bochum (Germany)

- 9002 0E **Femtosecond pulse generation from a two-section mode-locked quantum-dot laser using random population** [9002-13]
P. Finch, Tyndall National Institute (Ireland) and Cork Institute of Technology (Ireland); P. Blood, P. M. Smowton, A. Sobiesierski, Cardiff Univ. (United Kingdom); R. M. Gwilliam, Univ. of Surrey (United Kingdom); I. O'Driscoll, Tyndall National Institute (Ireland) and Cork Institute of Technology (Ireland)
- 9002 0F **Second harmonic pico-second pulse generation with mode-locked 1064nm DBR laser diodes** [9002-14]
A. Klehr, T. Prziwarka, D. Jedrzejczyk, O. Brox, F. Bugge, H. Wenzel, K. Paschke, G. Erbert, G. Tränkle, Ferdinand-Braun-Institut (Germany)

NITRIDES

- 9002 0H **Optically pumped deep-ultraviolet AlGaN multi-quantum-well lasers grown by metalorganic chemical vapor deposition (Invited Paper)** [9002-16]
Y.-S. Liu, T.-T. Kao, Md. M. Satter, Z. Lochner, X.-H. Li, S.-C. Shen, P. D. Yoder, T. Detchprohm, R. D. Dupuis, Georgia Institute of Technology (United States); Y. Wei, H. Xie, A. Fischer, F. A. Ponce, Arizona State Univ. (United States)
- 9002 0I **Influence of surface roughness on the optical mode profile in GaN-based violet ridge waveguide laser diodes** [9002-17]
K. Holc, A. Jakob, T. Weig, K. Köhler, O. Ambacher, Fraunhofer-Institut für Angewandte Festkörperphysik (Germany); U. T. Schwarz, Fraunhofer-Institut für Angewandte Festkörperphysik (Germany) and Albert-Ludwigs-Univ. Freiburg (Germany)
- 9002 0K **Absorption at large reverse bias in monolithic GaN-based short-pulse-multi-section laser diodes** [9002-19]
T. Weig, G. Lükens, K. Holc, K. Köhler, J. Wagner, Fraunhofer-Institut für Angewandte Festkörperphysik (Germany); U. T. Schwarz, Fraunhofer-Institut für Angewandte Festkörperphysik (Germany) and Albert-Ludwigs-Univ. Freiburg (Germany)

LASERS ON SILICON

- 9002 0U **Heterogeneously integrated lasers on silicon (Invited Paper)** [9002-29]
B. R. Koch, E. J. Norberg, J. E. Roth, B. Kim, A. Ramaswamy, R. S. Guzzon, J. Hutchinson, J.-H. Shin, J. Imamura, B. Gomez, G. Fish, A. Fang, Aurion, Inc. (United States)
- 9002 0X **Hybrid III-V on silicon lasers for photonic integrated circuits on silicon (Invited Paper)** [9002-32]
G.-H. Duan, C. Jany, A. Le Liepvre, A. Accard, M. Lamponi, D. Make, P. Kaspar, G. Levaufre, N. Girard, F. Lelarge, III-V Lab., Thales Research and Technology (France) and CEA-LETI (France); J.-M. Fedeli, S. Messaoudene, D. Bordel, S. Olivier, CEA-LETI-Minatec (France)

PHOTONIC BANDGAP AND MICROCAVITY

- 9002 0Z **Photonic crystal surface-emitting lasers as a pumping light source for second harmonic generation** [9002-34]
A. Watanabe, Hamamatsu Photonics K.K. (Japan); K. Hirose, Y. Kurosaka, Hamamatsu Photonics K.K. (Japan) and Kyoto Univ. (Japan); T. Sugiyama, Hamamatsu Photonics K.K. (Japan); Y. Liang, S. Noda, Kyoto Univ. (Japan)

MID-INFRARED LASERS: SB-BASED

- 9002 13 **Cascade pumping of GaSb-based type-I quantum well diode lasers (Invited Paper)** [9002-38]
L. Shterengas, R. Liang, G. Kipshidze, T. Hosoda, S. Suchalkin, G. Belenky, Stony Brook Univ. (United States)
- 9002 14 **Ultra-low input power long-wavelength GaSb type-I laser diodes at 2.7-3.0 μm** [9002-39]
A. Vizbaras, M. Greibus, E. Dvinelis, A. Trinkūnas, D. Kovalenkovas, I. Šimonytė, K. Vizbaras, Brolis Semiconductors UAB (Lithuania)
- 9002 16 **2-micron GaSb-based metamorphic laser grown on GaAs (Invited Paper)** [9002-41]
P. Apiratikul, L. He, R. P. Leavitt, N. P. Siwak, Univ. of Maryland, College Park (United States) and Lab. for Physical Sciences (United States); J. Duperre, C. J. K. Richardson, Lab. for Physical Sciences (United States)

MID-INFRARED QCLS II

- 9002 1A **AlAs/InAlAs-InGaAs QCLs grown by gas-source molecular-beam epitaxy (Invited Paper)** [9002-45]
W. T. Masselink, M. P. Semtsiv, Y. V. Flores, S. Kurlov, M. Elagin, G. Monastyrskyi, J.-F. Kischkat, A. Aleksandrova, Humboldt Univ. (Germany)

MID-INFRARED LASERS II

- 9002 1B **Interband cascade lasers for the mid-infrared spectral region (Invited Paper)** [9002-46]
S. Höfling, R. Weih, M. Dallner, M. Kamp, Julius-Maximilians-Univ. Würzburg (Germany)
- 9002 1C **High-power CW performance of 7-stage interband cascade lasers** [9002-47]
C. L. Canedy, J. Abell, C. D. Merritt, W. W. Bewley, C. S. Kim, U.S. Naval Research Lab. (United States); M. Kim, Sotera Defense Solutions, Inc. (United States); I. Vurgaftman, J. R. Meyer, U.S. Naval Research Lab. (United States)
- 9002 1D **Quantum band engineering of nitride semiconductors for infrared lasers (Invited Paper)** [9002-48]
O. Malis, C. Edmunds, D. Li, J. Shao, G. Gardner, Purdue Univ. (United States); W. Li, P. Fay, Univ. of Notre Dame (United States); M. J. Manfra, Purdue Univ. (United States)

- 9002 1E **High-performance InP-based InAs triangular quantum well lasers operating beyond 2 μm** [9002-49]
Y. Gu, Y. G. Zhang, Y. Y. Cao, X. Y. Chen, H. Li, L. Zhou, Shanghai Institute of Microsystem and Information Technology (China)

HIGH BRIGHTNESS/HIGH EFFICIENCY

- 9002 1F **High-power and high-efficiency broad-area diode laser emitting at 1.5 μm (Invited Paper)** [9002-50]
T. Garrod, D. Olson, M. Klaus, C. Zenner, C. Galstad, F. Brunet, Compound Photonics (United States); L. Mawst, D. Botez, Univ. of Wisconsin-Madison (United States)
- 9002 1G **Very high-power broad area laser diode with internal wavelength stabilization at 975 nm for Yb fibre laser pumping** [9002-51]
M. Krakowski, M. Lamponi, M. Lecomte, M. Maria, P. Resneau, Y. Robert, E. Vinet, M. Garcia, O. Parillaud, III-V Lab. (France)
- 9002 1H **Defect temperature kinetics during catastrophic optical damage in high power diode lasers** [9002-52]
M. Hempel, J. W. Tomm, Max-Born-Institut (Germany)
- 9002 1I **Cryogenic ultra-high power infrared diode laser bars (Invited Paper)** [9002-53]
P. Crump, C. Frevert, H. Hösler, F. Bugge, S. Knigge, W. Pittroff, G. Erbert, G. Tränkle, Ferdinand-Braun-Institut (Germany)
- 9002 1J **Realization of high-power narrow beam divergence in photonic-crystal surface-emitting laser** [9002-54]
K. Hirose, Y. Kurosaka, Hamamatsu Photonics K.K. (Japan) and Kyoto Univ. (Japan); A. Watanabe, T. Sugiyama, Hamamatsu Photonics K.K. (Japan); Y. Liang, S. Noda, Kyoto Univ. (Japan)

QCL ARRAYS/TUNABLE QCLS

- 9002 1N **Integrated widely tunable quantum cascade lasers with super-structure gratings** [9002-58]
D. Guo, X. Chen, Univ. of Maryland, Baltimore County (United States); J.-Y. Li, Princeton Univ. (United States); L. Cheng, T. Worchesky, F.-S. Choa, Univ. of Maryland, Baltimore County (United States)
- 9002 1O **InGaAs/InP-based Echelle mirror multiplexer using dual Rowland circle gratings for DFB QCL arrays in the mid-long infrared range** [9002-59]
L. J. Orbe, C. Gordon, G. Carpintero, Univ. Carlos III de Madrid (Spain); G. Maisons, M. Carras, III-V Lab. (France)

MID-INFRARED QCLS III

- 9002 1R **The role of electron temperature in the leakage current in QCLs and its impact on the quantum efficiency** [9002-62]
Y. V. Flores, S. S. Kurlov, M. Elagin, M. P. Semtsiv, W. T. Masselink, Humboldt Univ. (Germany)

- 9002 1T **Non-resonant optical modulation of quantum cascade laser and its application potential in infrared spectroscopy (Invited Paper) [9002-64]**
T. Yang, C. Tian, Stevens Institute of Technology (United States); G. Chen, Chongqing Univ. (China); R. Martini, Stevens Institute of Technology (United States)

Author Index

Conference Committee

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Session Chairs

- 1 Quantum Dots
Luke F. Lester, Virginia Polytechnic Institute and State University (United States)
- 2 New Materials and Grating Controlled
Luke Mawst, University of Wisconsin-Madison (United States)
- 3 Mode Locked
Johann Peter Reithmaier, Universität Kassel (Germany)
- 4 Nitrides
Michael Kneissl, Technische Universität Berlin (Germany)
- 5 Mid-Infrared QCLs I
Alexey A. Belyanin, Texas A&M University (United States)
- 6 Terahertz QCLs
Jerome Faist, ETH Zurich (Switzerland)
- 7 Lasers on Silicon
Jonathan K. Doylend, Intel Corporation (United States)
- 8 Photonic Bandgap and Microcavity
Kresten Yvind, Technical University of Denmark (Denmark)
- 9 Mid-Infrared Lasers: Sb-based
Oana Malis, Purdue University (United States)
- 10 Mid-Infrared QCLs II
Jerry R. Meyer, U.S. Naval Research Laboratory (United States)
- 11 Mid-Infrared Lasers II
William T. Masselink, Humboldt-Universität zu Berlin (Germany)
- 12 High Brightness/High Efficiency
Gary A. Evans, Southern Methodist University (United States)
- 13 QCL Arrays/Tunable QCLs
Qijie Wang, Nanyang Technological University (Singapore)
- 14 Mid-Infrared QCLs III
Christian J. Pflügl, EOS Photonics (United States)